



Application Serial No. 10/593,577

Abstract

~~The limiter of the invention uses as a diode a stacked gate thin film transistor (TFT) including a floating gate. When the TFT including a floating gate is used, the threshold voltage V_{th} may be corrected by controlling the amount of charge accumulated in the floating gate even in the case where there are variations in the threshold voltages V_{th} of the TFT.~~

By using a stacked gate transistor including a floating gate in a limiter, a threshold voltage V_{th} of the stacked gate transistor can be corrected by controlling the amount of charge accumulated in the floating gate of the stacked gate transistor even in the case where there are variations in the threshold voltage V_{th} of the stacked gate transistor.